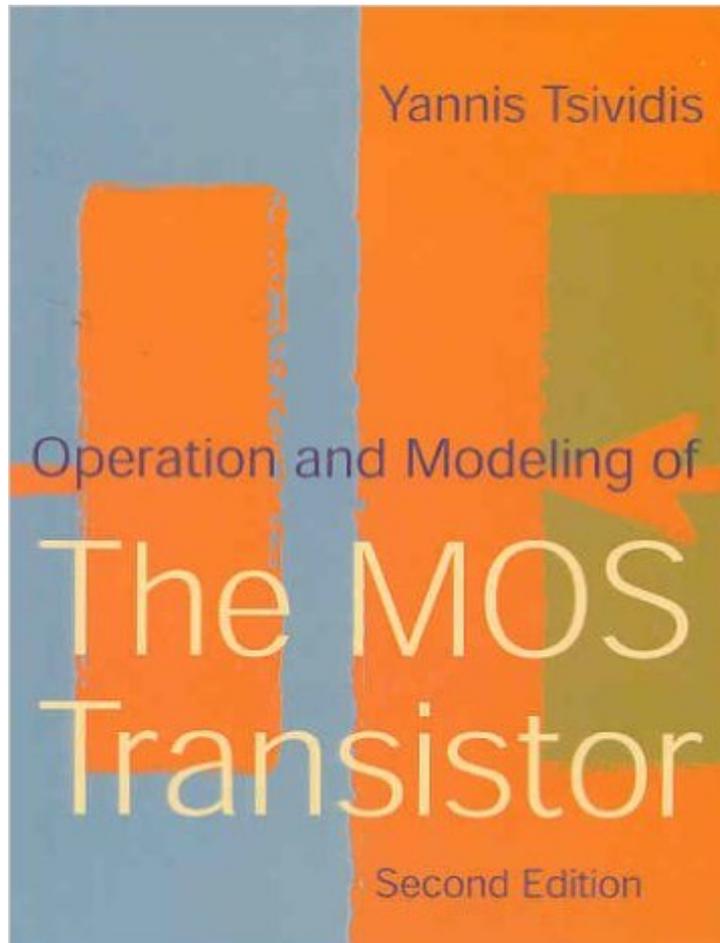


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# Operation & Modeling Of The MOS Transistor



## Synopsis

Operation end Modeling of the MOS Transistor, 2/e carefully leads from physical principles to relevant working models of the MOS Transistors device. Models range from the very simple to sophisticated with the connections between models of successive levels clearly identified. Intuitive understanding is provided through extensive discussions.

## Book Information

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## Customer Reviews

I don't usually write reviews unless the book is either very poor or very good. This is one of the best books on my shelf. If you want to know the MOS transistor this is the book. Well researched, excellent explanations, excellent appendices. Other authors of technical books should use this as an example of how to write a good technical book.

I am a graduate student with main area of interest in Mixed mode design, testing and device modelling. This book was suggested to me by my professor. It is the book for MOSFET. I have read many books on this topic like Tyagi, Foty, massobrio etc but this book stands apart. It is a very well written book. Its progress is very logical going from two terminal device to four terminal device with very good explanation of the physics. More importantly the emphasis on the approximations made makes things clearer..... For a person working with Mosfets it is a must.....

Just reading the Preface to this book, I fell in love with the author. I completely agree that sometimes the most rigorous and careful treatment of a subject actually makes it possible to study the material faster!! What always frustrated me and slowed me down in reading other books was the sloppiness and hand waving. It's amazing that many Ph.Ds and even authors of famous books like Uyemura's "Fundamentals of MOS ICs" don't understand the simple body effect, and talk about complete nonsense showing a 2 terminal capacitor with  $V_b$  applied to the bulk, and saying that the  $V_t$  will now change by the  $\sqrt{V_b}$  body effect. They don't understand that the body effect is a 3 terminal effect and in 2 terminals if you apply  $V_b$  to bulk then your  $V_t$  will have to increase by  $V_b$ --NOT  $\sqrt{V_b}$ !!! This book is a delight. Just the material on contact potentials was worth the money.If you are serious about really understanding MOSFETs, if you hate non-sense and hand waving, then this book is for you.

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